

Supporting Information

Stabilization of wide band-gap p-type wurtzite MnTe thin films on amorphous substrates

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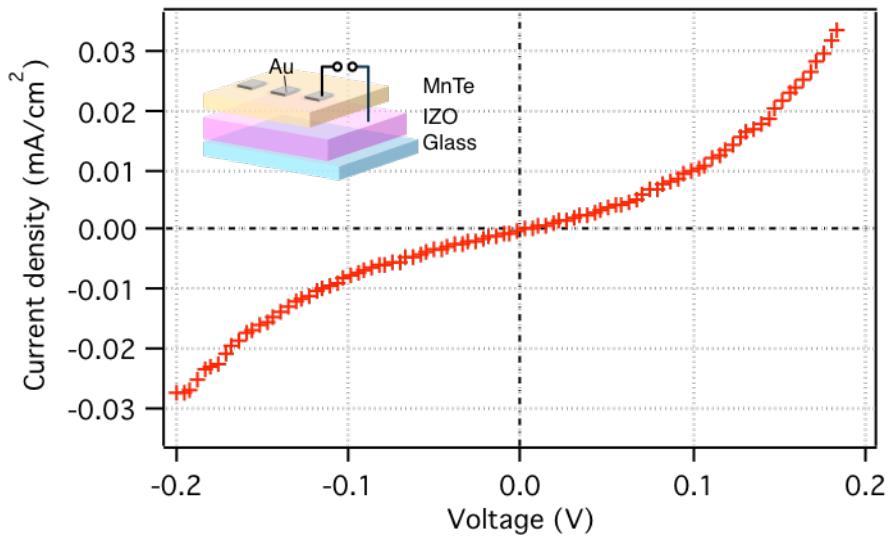


Figure S1: JV measurements on device stacks of WZ-type MnTe on a-IZO

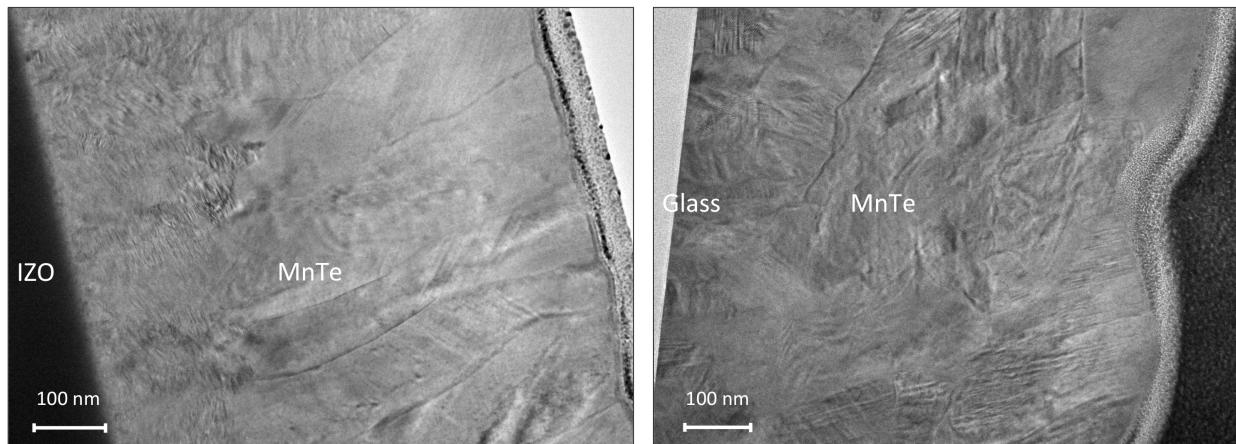


Figure S2: TEM micrographs of MnTe on a-IZO and Glass.

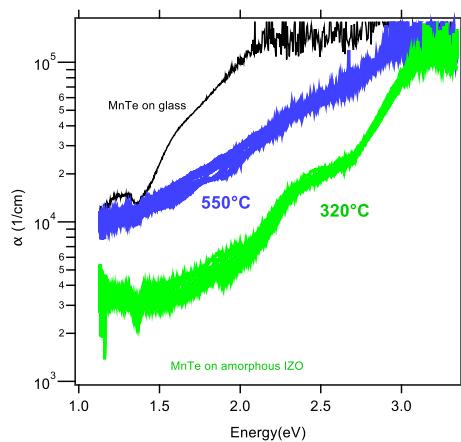


Figure S3: Deposition at high temperatures leads to secondary phases and increased sub band gap absorption. Shown is NC-MnTe on glass for reference as well as data for 11 different samples each for 550°C and 320°C deposited on a-IZO